

H5N2501LD, H5N2501LS, H5N2501LM

Silicon N Channel MOS FET High Speed Power Switching

R07DS0056EJ0300 (Previous: REJ03G1250-0200)

> Rev.3.00 Jul 23, 2010

Features

- Low on-resistance $R_{DS(on)} = 0.14 \Omega$ typ. (at $I_D = 9$ A, $V_{GS} = 10$ V, Ta = 25°C)
- Low leakage current
- · High speed switching

Outline

RENESAS Package code: PRSS0004AE-A (Package name LDPAK(L))

RENESAS Package code: PRSS0004AE-B (Package name LDPAK(S)-(1))

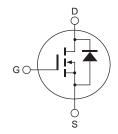
1 2 3 H5N2501LD 1₂₃

H5N2501LS

RENESAS Package code: PRSS0004AE-C (Package name LDPAK(S)-(2))



H5N2501LM



- 1. Gate
- 2. Drain
- 3. Source
- 4. Drain

Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to Source voltage	V _{DSS}	250	V
Gate to Source voltage	V _{GSS}	±30	V
Drain current	I _D	18	Α
Drain peak current	I _{D (pulse)} Note1	72	Α
Body-Drain diode reverse Drain current	I _{DR}	18	A
Avalanche current	I _{AP} Note3	18	A
Avalanche energy	E _{AR} Note3	20.25	mJ
Channel dissipation	Pch Note2	75	W
Channel to case thermal impedance	θch-c	1.67	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	−55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

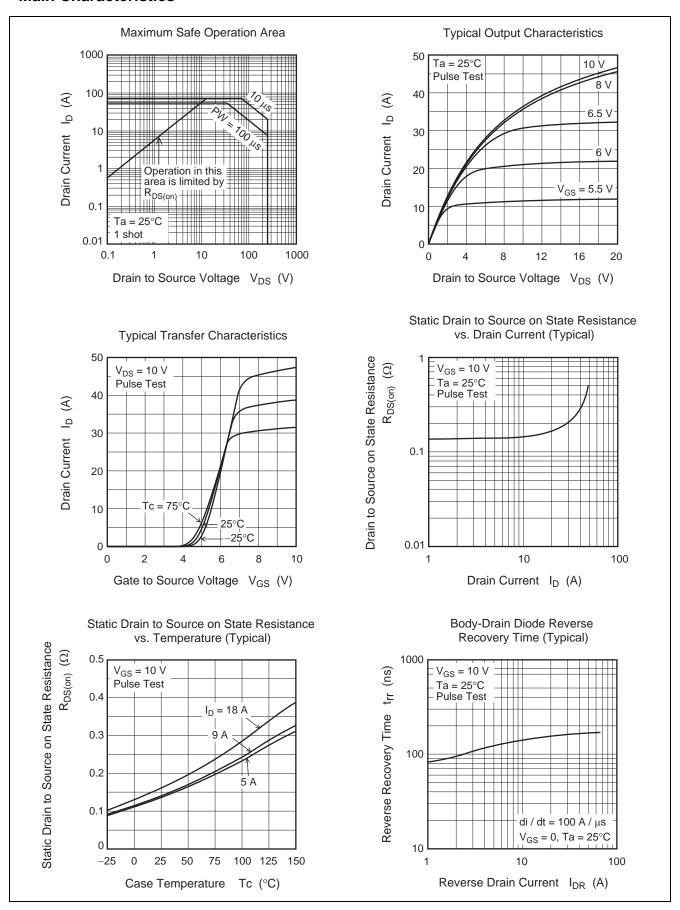
Electrical Characteristics

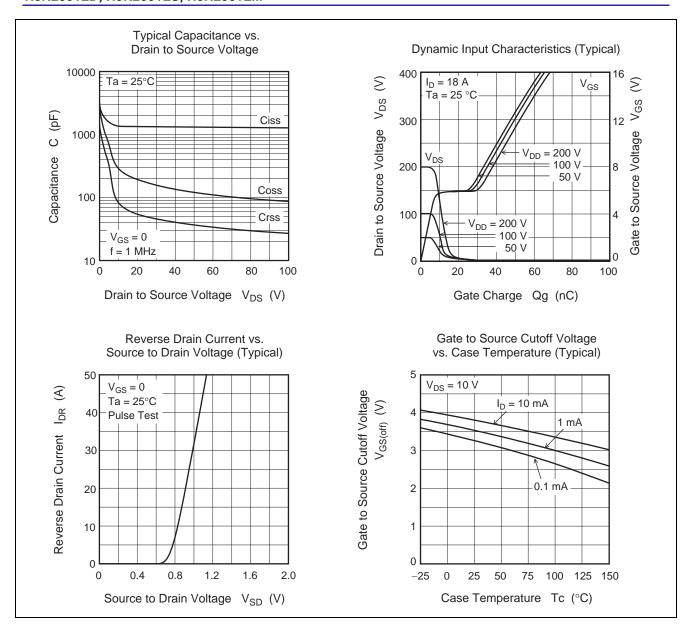
 $(Ta = 25^{\circ}C)$

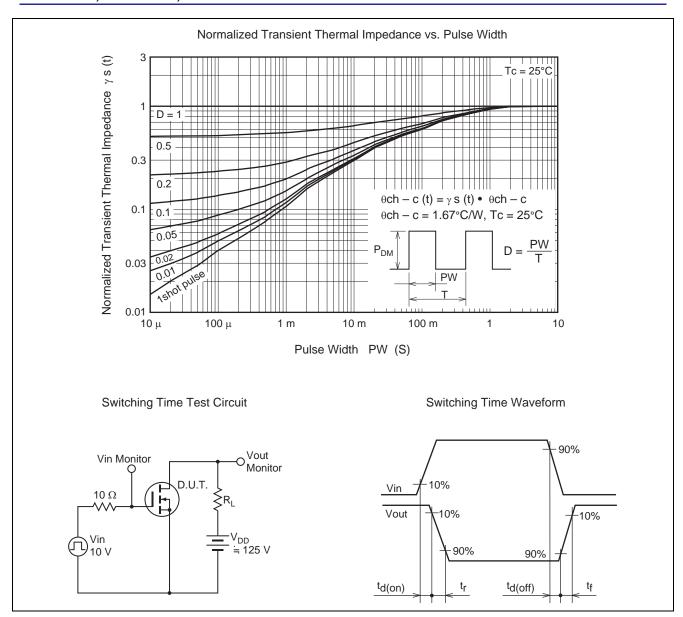
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to Source breakdown voltage	$V_{(BR)DSS}$	250	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Zero Gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 250 \text{ V}, V_{GS} = 0$
Gate to Source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$
Gate to Source cutoff voltage	$V_{GS(off)}$	3.0	_	4.5	V	$V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$
Forward transfer admittance	yfs	8	14	_	S	$I_D = 9 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static Drain to Source on state	R _{DS(on)}	_	0.14	0.18	Ω	$I_D = 9 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance						
Input capacitance	Ciss	_	1350	_	pF	V _{DS} = 25 V
Output capacitance	Coss	_	170	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss	_	50	_	pF	
Turn-on delay time	t _{d(on)}	_	30	_	ns	I _D = 9 A
Rise time	t _r	_	65	_	ns	V _{GS} = 10 V
Turn-off delay time	t _{d(off)}	_	95	_	ns	$R_L = 13.9 \Omega$
Fall time	t _f	_	18	_	ns	$Rg = 10 \Omega$
Total Gate charge	Qg	_	45	_	nC	V _{DD} = 200 V
Gate to Source charge	Qgs	_	8	_	nC	V _{GS} = 10 V I _D = 18 A
Gate to Drain charge	Qgd	_	22	_	nC	
Body-Drain diode forward voltage	V_{DF}	_	0.9	1.4	V	$I_F = 18 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-Drain diode reverse recovery time	t _{rr}	_	160	_	ns	I _F = 18 A, V _{GS} = 0
Body-Drain diode reverse recovery charge	Q _{rr}	_	1.0	_	μС	di _F /dt = 100 A/μs

Notes: 4. Pulse test

Main Characteristics

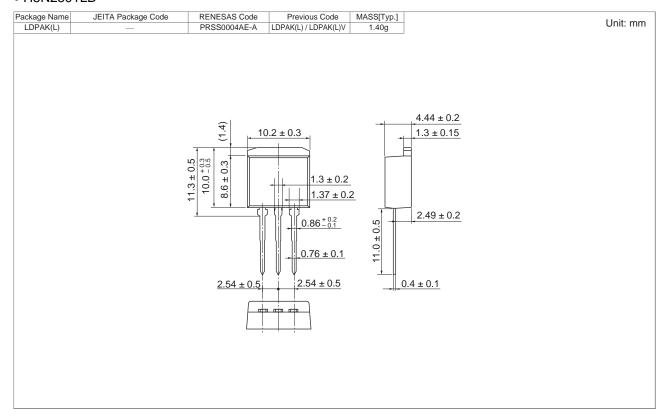




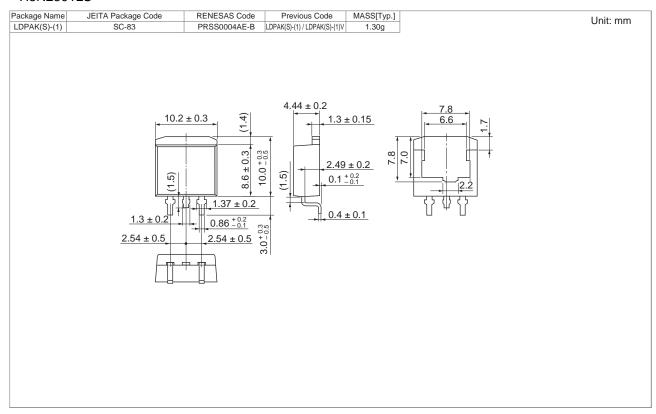


Package Dimensions

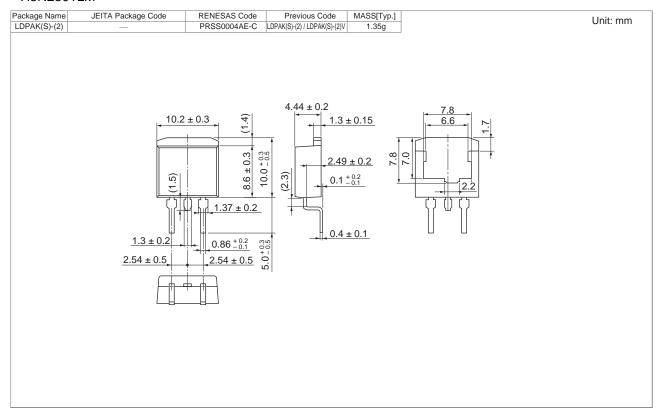
• H5N2501LD



• H5N2501LS



• H5N2501LM



Ordering Information

Part No.	Quantity	Shipping Container
H5N2501LD-E	300 pcs	Box (Tube)
H5N2501LSTL-E	1000 pcs	Taping
H5N2501LMTL-E	1000 pcs	Taping

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